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				Filing Date	July 16, 2003
				First Named Inventor:	Aaditya Mahajan
				Examiner name: unknown	GROUP: unknown
Sheet	1	of	1	Attorney Docket Number	TRQ-12957

U.S. PUBLISHED PATENT APPLICATIONS

Examiner Initials*	Cited No. ¹	U.S. Patent Document Number Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cited No. ¹	Foreign Patent Document Office ³ Number ⁴ Kind Code ⁵ (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear	T ⁶

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Bollaert et al., "Metamorphic In _{0.4} Al _{0.6} As/In _{0.4} Ga _{0.6} As HEMT's on GaAs Substrate", IEEE Electron Device Letters, Vol. 20, No. 3, March 1999, pp. 123-125.
	Dumka et al., "High Performance 0.35 μ m Gate-Length Monolithic Enhancement/Depletion-Mode Metamorphic In _{0.52} Al _{0.48} As/In _{0.53} Ga _{0.47} As HEMTs on GaAs Substrates", IEEE Electron Device Letters, Vol. 22, No. 8, August 2001, pp. 364-366.
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EXAMINER	DATE CONSIDERED
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